

L Number	Hits	Search Text	DB	Time stamp
-	2	semiconductor and (deposit\$4 same (ion with beam) same siloxane same organometallic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 13:27
-	2	("6459955").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 14:14
-	2322	semiconductor and (ion with beam with sputtering)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 14:27
-	2	(semiconductor and (ion with beam with sputtering)) and (siloxane and organometallic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 14:27
-	1	((semiconductor and (ion with beam with sputtering)) and (siloxane and organometallic)) not (semiconductor and (deposit\$4 same (ion with beam) same siloxane same organometallic))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 14:28
-	26	(438/961).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 14:35
-	3	semiconductor and (epitaxy with MBE) and (siloxane and organmetal\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 14:59
-	5	semiconductor and (deposit\$4 same siloxane same organometal\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 15:23
-	0	semiconductor and (ion with beam) and (precursor with silane) and (precursor with ((tungsten or platinum or W or Pt) adj (C or carbon or methyl\$5)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 15:56
-	4	semiconductor and (ion with beam) and (precursor with silane) and (precursor with ((tungsten or platinum or W or Pt)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 15:58
-	1	semiconductor and (ion with beam) and (precursor with siloxane) and (precursor with ((tungsten or platinum or W or Pt)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 15:59
-	1	semiconductor and (ion with beam) and (precursor with organ\$4 with (silicon or silane)) and (precursor with ((tungsten or platinum or W or Pt)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 16:02
-	9212	(438/758-794).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 16:03
-	333	((438/758-794).CCLS.) and siloxane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/25 16:03

	0	((438/758-794).CCLS.) and siloxane) and metallorganic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 16:03
	16	((438/758-794).CCLS.) and metallorganic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 16:03
	181	((438/758-794).CCLS.) and siloxane) and (tungsten or W or platinum or Pt)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 16:05
	19	((438/758-794).CCLS.) and (siloxane same (tungsten or W or platinum or Pt))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 16:08
	4	("5827786") or ("4876112").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/25 16:51
	11	("4845054" "4851097" "4874460" "4876112" "4930439" "4950498" "4976843" "5083033" "5148024" "5196102" "5429730").PN.	USPAT	2003/03/25 16:08
	2	5827786.URPN.	USPAT	2003/03/25 16:15
	5	("4042006" "4372989" "4609809" "4612085" "4615904").PN.	USPAT	2003/03/25 16:16
	41	4876112.URPN.	USPAT	2003/03/25 16:17
	41	4876112.URPN.	USPAT	2003/03/25 16:50
	107	semiconductor and resistor and FIB	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 13:55
	65	semiconductor and resistor and ((ion with beam) with FIB)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 13:57
	9	semiconductor and resistor and (deposit\$4 with FIB)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 13:59
	310	semiconductor and resistor and (deposit\$4 with ion with beam)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 14:00
	1724	semiconductor and (resistor or resistance) and (deposit\$4 with ion with beam)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 14:02
	58	semiconductor and (resistor or resistance) and (deposit\$4 with FIB)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 14:02
	49	(semiconductor and (resistor or resistance) and (deposit\$4 with FIB)) not (semiconductor and resistor and (deposit\$4 with FIB))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/26 14:05

	2725	semiconductor and (high with resistance).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/26 14:08
	43	semiconductor and (highly with resistive).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/26 14:06
	2768	(semiconductor and (high with resistance).ti.) or (semiconductor and (highly with resistive).ti.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/26 14:06
	19	((semiconductor and (high with resistance).ti.) or (semiconductor and (highly with resistive).ti.)) and siloxane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/26 14:06
	549	semiconductor and ((resistive or resistance) adj layer).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/26 14:10
	0	(semiconductor and ((resistive or resistance) adj layer).ti.) and siloxane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/26 14:11
	0	(semiconductor and ((resistive or resistance) adj layer).ti.) and (organ\$3 adj silane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/26 14:16
	0	(semiconductor and ((resistive or resistance) adj layer).ti.) and (organ\$3 adj silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/26 14:18
	15	semiconductor and (((resistive or resistivity or resistance or resistor) adj (layer or material)) same ((focused adj ion adj beam) or FIB))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/26 16:00
	2	("5827786").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/26 16:00
	11	("4845054" "4851097" "4874460" "4876112" "4930439" "4950498" "4976843" "5083033" "5148024" "5196102" "5429730").PN.	USPAT	2003/03/26 16:00
	2	5827786.URPN.	USPAT	2003/03/26 16:07
	111	semiconductor and (ion with beam with deposition) and (organ\$5 with metal\$3) and (siloxane or silane)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/28 11:56
	0	oranometalsiloxane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/28 11:45
	2	metalsiloxane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/28 11:45

-	0	metallorganosiloxane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2003/03/28 11:46
-	0	metallorganicsiloxane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2003/03/28 11:52
-	0	metallorganocsilane	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2003/03/28 11:52
-	6	semiconductor and (ion with beam with deposition) and ((organ\$5 with metal\$3) same (siloxane or silane))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2003/03/28 13:42
-	4	(("4876112") or ("5073033") or ("5104684") or ("5827786")).PN.	USPAT	2003/03/28 13:44
-	4	(("4876112") or ("0503033") or ("5104684") or ("5827786")).PN.	USPAT	2003/03/28 13:45
-	4	((("4876112") or ("5083033") or ("5104684") or ("5827786")) .PN.	USPAT	2003/03/28 13:45